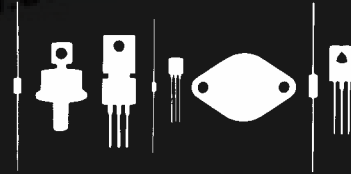


Central
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2N4256

NPN SILICON TRANSISTOR

JEDEC TO-92 CASE (ECB)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4256 type is a Silicon NPN Planar Epitaxial Transistor designed for low level medium speed switching applications.

MAXIMUM RATINGS (T_A = 25°C)

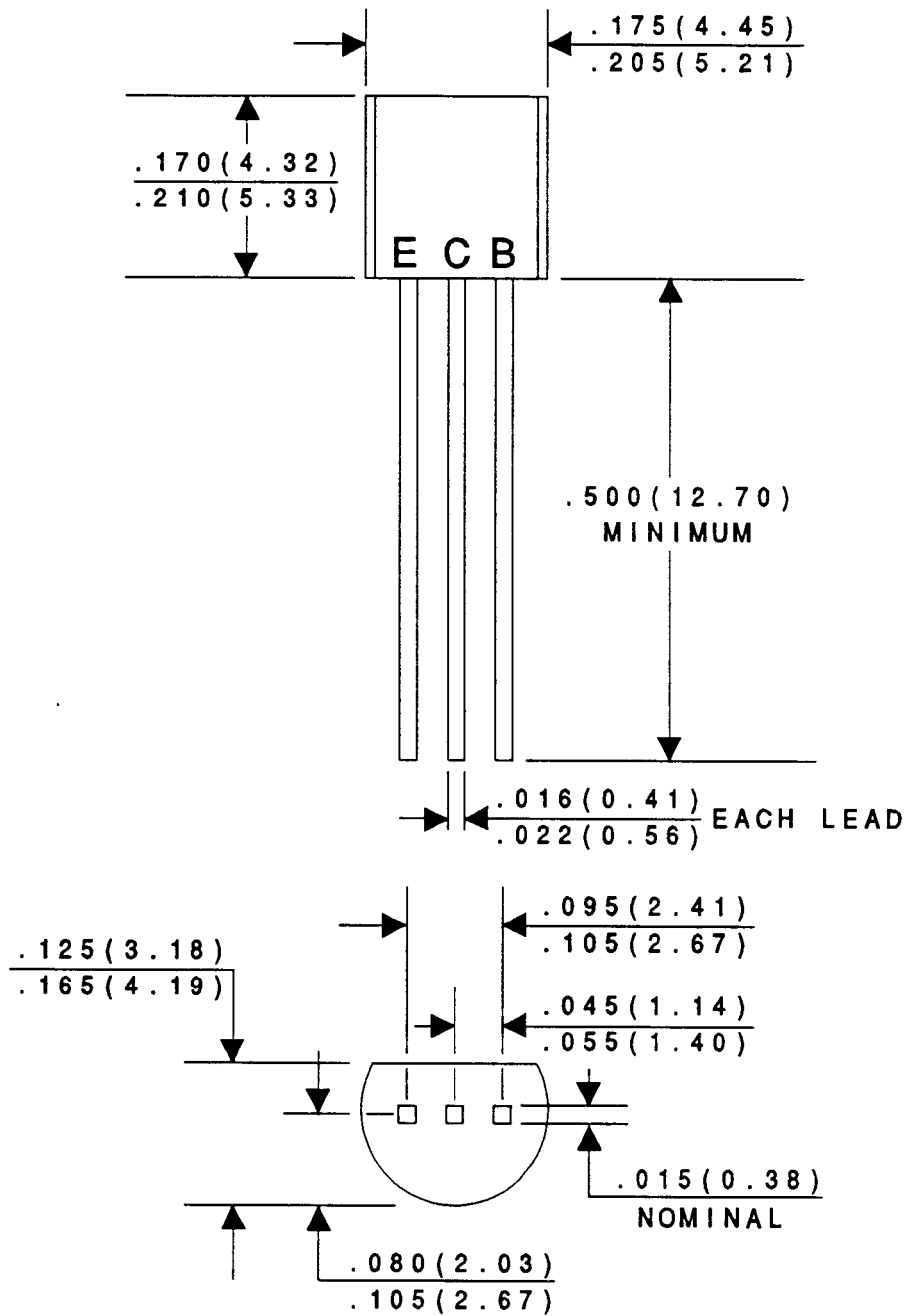
	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	30	V
Collector-Emitter Voltage	V _{CES}	30	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	100	mA
Power Dissipation	P _D	625	mW
Power Dissipation (T _C = 25°C)	P _D	1.5	W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	200	°C/W
Thermal Resistance	θ _{JC}	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} = 30V			500	nA
I _{CBO}	V _{CE} = 18V, T _A = 100°C			15	µA
I _{CES}	V _{CE} = 30V			500	nA
I _{EBO}	V _{EB} = 5.0V			500	nA
BV _{CBO}	I _C = 100µA	30			V
BV _{CES}	I _C = 1.0mA	30			V
BV _{EBO}	I _E = 100µA	5.0			V
V _{CE(SAT)}	I _C = 0.1mA, I _B = 2.0µA			0.2	V
V _{CE(SAT)}	I _C = 1.0mA, I _B = 20µA			0.2	V
V _{CE(SAT)}	I _C = 10mA, I _B = 200µA			0.2	V
V _{CE(SAT)}	I _C = 50mA, I _B = 2.5mA			0.2	V
V _{BE(SAT)}	I _C = 50mA, I _B = 2.5mA			0.92	V
h _{FE}	V _{CE} = 4.5V, I _C = 2.0mA	100		500	
h _{FE}	V _{CE} = 0.2V, I _C = 10mA	60			
h _{FE}	V _{CE} = 0.2V, I _C = 50mA	20			
f _T	V _{CE} = 1.0V, I _C = 10mA		200		MHz
C _{ib}	V _{BE} = 0.5V, I _C = 0, f = 1.0MHz		10		pF
C _{ob}	V _{CB} = 10V, I _E = 0, f = 1.0MHz			4.0	pF
Q _{SB}	I _C = 10mA, I _B = 0.32mA			600	pC
t _{on}	V _{CC} = 6.0V, I _C = 10mA		4.0		ns
t _{off}	V _{CC} = 6.0V, I _C = 10mA			3.5	µs
t _{on}	V _{CC} = 6.0V, I _C = 10mA, I _{B1} = 0.32mA, I _{B2} = 54µA			180	ns
t _{off}	V _{CC} = 6.0V, I _C = 10mA, I _{B1} = 0.32mA, I _{B2} = 54µA			3.5	µs



JEDEC TO-92 CASE - MECHANICAL DIMENSIONS



All Dimensions in Inches (mm).